Old Company Name in Catalogs and Other Documents

On April 1st, 2010, NEC Electronics Corporation merged with Renesas Technology Corporation, and Renesas Electronics Corporation took over all the business of both companies. Therefore, although the old company name remains in this document, it is a valid Renesas Electronics document. We appreciate your understanding.

Renesas Electronics website: http://www.renesas.com

April 1st, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

Send any inquiries to http://www.renesas.com/inquiry.

Notice

- 1. All information included in this document is current as of the date this document is issued. Such information, however, is subject to change without any prior notice. Before purchasing or using any Renesas Electronics products listed herein, please confirm the latest product information with a Renesas Electronics sales office. Also, please pay regular and careful attention to additional and different information to be disclosed by Renesas Electronics such as that disclosed through our website.
- Renesas Electronics does not assume any liability for infringement of patents, copyrights, or other intellectual property rights of third parties by or arising from the use of Renesas Electronics products or technical information described in this document. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
- 3. You should not alter, modify, copy, or otherwise misappropriate any Renesas Electronics product, whether in whole or in part.
- 4. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation of these circuits, software, and information in the design of your equipment. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from the use of these circuits, software, or information.
- 5. When exporting the products or technology described in this document, you should comply with the applicable export control laws and regulations and follow the procedures required by such laws and regulations. You should not use Renesas Electronics products or the technology described in this document for any purpose relating to military applications or use by the military, including but not limited to the development of weapons of mass destruction. Renesas Electronics products and technology may not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations.
- 6. Renesas Electronics has used reasonable care in preparing the information included in this document, but Renesas Electronics does not warrant that such information is error free. Renesas Electronics assumes no liability whatsoever for any damages incurred by you resulting from errors in or omissions from the information included herein.
- 7. Renesas Electronics products are classified according to the following three quality grades: "Standard", "High Quality", and "Specific". The recommended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below. You must check the quality grade of each Renesas Electronics product before using it in a particular application. You may not use any Renesas Electronics product for any application categorized as "Specific" without the prior written consent of Renesas Electronics. Further, you may not use any Renesas Electronics. Renesas Electronics shall not be in any way liable for any damages or losses incurred by you or third parties arising from the use of any Renesas Electronics product for an application categorized as "Specific" or for which the product is not intended where you have failed to obtain the prior written consent of Renesas Electronics. The quality grade of each Renesas Electronics product is "Standard" unless otherwise expressly specified in a Renesas Electronics data sheets or data books, etc.
 - "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; and industrial robots.
 - "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control systems; anti-disaster systems; anticrime systems; safety equipment; and medical equipment not specifically designed for life support.
 - "Specific": Aircraft; aerospace equipment; submersible repeaters; nuclear reactor control systems; medical equipment or systems for life support (e.g. artificial life support devices or systems), surgical implantations, or healthcare intervention (e.g. excision, etc.), and any other applications or purposes that pose a direct threat to human life.
- 8. You should use the Renesas Electronics products described in this document within the range specified by Renesas Electronics, especially with respect to the maximum rating, operating supply voltage range, movement power voltage range, heat radiation characteristics, installation and other product characteristics. Renesas Electronics shall have no liability for malfunctions or damages arising out of the use of Renesas Electronics products beyond such specified ranges.
- 9. Although Renesas Electronics endeavors to improve the quality and reliability of its products, semiconductor products have specific characteristics such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Further, Renesas Electronics products are not subject to radiation resistance design. Please be sure to implement safety measures to guard them against the possibility of physical injury, and injury or damage caused by fire in the event of the failure of a Renesas Electronics product, such as safety design for hardware and software including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult, please evaluate the safety of the final products or system manufactured by you.
- 10. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. Please use Renesas Electronics products in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. Renesas Electronics assumes no liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
- 11. This document may not be reproduced or duplicated, in any form, in whole or in part, without prior written consent of Renesas Electronics.
- 12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products, or if you have any other inquiries.
- (Note 1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its majorityowned subsidiaries.
- (Note 2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

RENESAS

R1EX25002ASA00I/R1EX25004ASA00I R1EX25002ATA00I/R1EX25004ATA00I

Serial Peripheral Interface 2k EEPROM (256-word \times 8-bit) 4k EEPROM (512-word \times 8-bit) Electrically Erasable and Programmable Read Only Memory

> REJ03C0361-0002 Preliminary Rev.0.02 Jan.9.2009

Description

R1EX25xxx Series is the Serial Peripheral Interface compatible (SPI) EEPROM (Electrically Erasable and Programmable ROM). It realizes high speed, low power consumption and a high level of reliability by employing advanced MONOS memory technology and CMOS process and low voltage circuitry technology. It also has a 16-byte page programming function to make it's write operation faster.

Features

- Single supply: 1.8 V to 5.5 V
- Serial Peripheral Interface compatible (SPI bus)
 SPI mode 0 (0,0), 3 (1,1)
- Clock frequency: 5 MHz (2.5 V to 5.5 V), 3 MHz (1.8 V to 5.5 V)
- Power dissipation:
 - Standby: 2µA (max)
 - Active (Read): 2 mA (max)
 - Active (Write): 2.5 mA (max)
- Automatic page write: 16-byte/page
- Write cycle time: 5 ms
- Endurance: 1,000k Cycles @25 °C
- Data retention: 100 Years @25 °C
- Small size packages: SOP-8pin, TSSOP-8pin
- Shipping tape and reel
 - TSSOP-8pin: 3,000 IC/reel
 - SOP-8pin : 2,500 IC/reel
- Temperature range: -40 to +85 °C
- Lead free product.

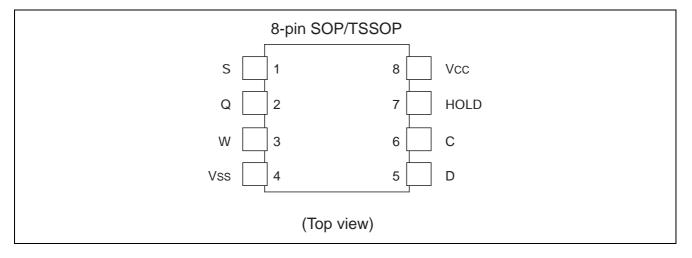
Preliminary: The specifications of this device are subject to change without notice. Please contact your nearest Renesas Technology's Sales Dept. regarding specifications



Ordering Information

Type No.	Internal organization	Operating voltage	Frequency	Package
R1EX25002ASA00I	2-kbit (256 \times 8-bit)	1.8 V to 5.5 V	5 MHz (2.5 V to 5.5 V)	150mil 8-pin plastic SOP PRSP0008DF-B
R1EX25004ASA00I	4-kbit (512 × 8-bit)		(2.5 V (0 5.5 V) 3 MHz	(FP-8DBV)
			(1.8 V to 5.5V)	Lead free
R1EX25002ATA00I	2-kbit (256 × 8-bit)	1.8 V to 5.5 V	5 MHz	8-pin plastic TSSOP
			(2.5 V to 5.5 V)	PTSP0008JC-B
R1EX25004ATA00I	4-kbit (512 × 8-bit)		3 MHz	(TTP-8DAV)
			(1.8 V to 5.5 V)	Lead free

Pin Arrangement

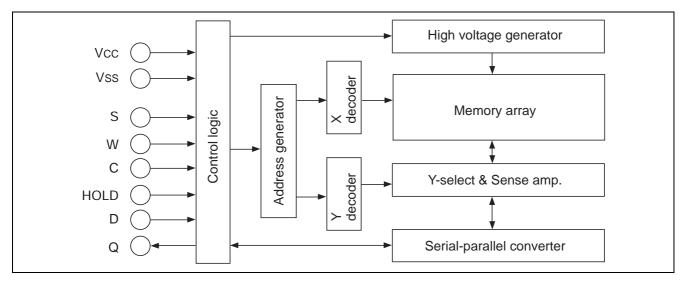


Pin Description

Pin name	Function
С	Serial clock
D	Serial data input
Q	Serial data output
S	Chip select
W	Write protect
HOLD	Hold
V _{cc}	Supply voltage
V _{SS}	Ground



Block Diagram



Absolute Maximum Ratings

Symbol	Value	Unit
V _{CC}	-0.6 to + 7.0	V
V _{IN}	-0.5^{*2} to $+7.0^{*3}$	V
Topr	-40 to +85	°C
Tstg	-55 to +125	°C
	V _{CC} V _{IN} Topr	V_{CC} -0.6 to + 7.0 V_{IN} $-0.5*^2$ to +7.0* ³ Topr -40 to +85

Notes: 1. Including electrical characteristics and data retention.

2. V_{IN} (min): -3.0 V for pulse width \leq 50 ns.

3. Should not exceed V_{CC} + 1.0 V.

DC Operating Conditions

Parameter	Symbol	Min	Тур	Max	Unit
Supply voltage	V _{CC}	1.8	—	5.5	V
	V _{SS}	0	0	0	V
Input voltage	V _{IH}	$V_{CC} imes 0.7$	—	$V_{CC} + 0.5^{*2}$	V
	V _{IL}	-0.3* ¹	—	$V_{CC} imes 0.3$	V
Operating temperature range	Topr	-40		+85	°C

Notes: 1. V_{IN} (min): -1.0 V for pulse width \leq 50 ns.

2. V_{IN} (max): V_{CC} + 1.0 V for pulse width \leq 50 ns.

Capacitance (Ta = +25°C, f = 1 MHz)

Parameter	Symbol	Min	Тур	Max	Unit	l est conditions
Input capacitance (D,C, S, W, HOLD)	Cin* ¹ -	_	_	6.0	pF	Vin = 0 V
Output capacitance (Q)	C _{I/O} * ¹ -	_		8.0	pF	Vout = 0 V

Note: 1. Not 100% tested.

Memory cell characteristics (V_{CC} = 1.8 V to 5.5 V)

	Ta=25 °C	Та=85 °С	Notes
Endurance	1,000k Cycles min.	100k Cycles min	1
Data retention	100 Years min.	10 Years min.	1

Notes: 1. Not 100% tested



DC Characteristics

Parameter		Symbol	Min	Max	Unit	Test conditions
Input leakage current		I _{LI}	—	2	μA	$V_{CC} = 5.5 \text{ V}, V_{IN} = 0 \text{ to } 5.5 \text{ V}$ (S, D, C, HOLD, W)
Output leakage current		I _{LO}		2	μA	$V_{CC} = 5.5 \text{ V}, V_{OUT} = 0 \text{ to } 5.5 \text{ V}$ (Q)
V _{CC} current	Standby	I _{SB}	—	2	μA	$V_{IN} = V_{SS} \text{ or } V_{CC},$ $V_{CC} = 5.5 \text{ V}$
	Active	I _{CC1}		2	mA	$\label{eq:V_CC} \begin{split} V_{CC} &= 5.5 \text{ V}, \text{ Read at 5 MHz} \\ V_{\text{IN}} &= V_{CC} \times 0.1 / V_{CC} \times 0.9 \\ Q &= \text{OPEN} \end{split}$
		I _{CC2}		2.5	mA	$V_{CC} = 5.5 \text{ V}, \text{ Write at 5 MHz}$ $V_{IN} = V_{CC} \times 0.1 / V_{CC} \times 0.9$
Output voltage		V _{OL1}	—	0.4	V	$V_{CC} = 5.5 \text{ V}, \text{ I}_{OL} = 2 \text{ mA}$
		V _{OL2}	—	0.4	V	$V_{CC} = 2.5 \text{ V}, I_{OL} = 1.5 \text{ mA}$
		V _{OH1}	$V_{CC} imes 0.8$	—	V	$V_{CC} = 5.5 \text{ V}, \text{ I}_{OH} = -2 \text{ mA}$
		V _{OH2}	$V_{CC} imes 0.8$	_	V	$V_{CC} = 2.5 \text{ V}, \text{ I}_{OH} = -0.4 \text{ mA}$



AC Characteristics

Test Conditions

- Input pules levels:
 - $--V_{\rm IL} = V_{\rm CC} \times 0.2$
 - ---- $V_{IH} = V_{CC} \times 0.8$
- Input rise and fall time: ≤ 10 ns
- Input and output timing reference levels: $V_{CC} \times 0.3, \, V_{CC} \times 0.7$
- Output reference levels: $V_{CC} \times 0.5$
- Output load: 100 pF

 $(Ta = -40 \text{ to } +85^{\circ}\text{C}, V_{CC} = 2.5 \text{ V to } 5.5 \text{ V})$

Parameter	Symbol	Alt	Min	Max	Unit	Notes
Clock frequency	f _C	f _{scк}	—	5	MHz	
S active setup time	t _{SLCH}	t _{CSS1}	90	_	ns	
S not active setup time	t _{SHCH}	t _{CSS2}	90		ns	
S deselect time	t _{SHSL}	t _{cs}	90		ns	
S active hold time	t _{CHSH}	t _{CSH}	90	_	ns	
S not active hold time	t _{CHSL}	_	90	—	ns	
Clock high time	t _{CH}	t _{CLH}	90	—	ns	1
Clock low time	t _{CL}	t _{CLL}	90	—	ns	1
Clock rise time	t _{CLCH}	t _{RC}	—	1	μs	2
Clock fall time	t _{CHCL}	t _{FC}	—	1	μs	2
Data in setup time	t _{DVCH}	t _{DSU}	20	—	ns	
Data in hold time	t _{CHDX}	t _{DH}	30	—	ns	
Clock low hold time after HOLD not active	t _{HHCH}		70		ns	
Clock low hold time after HOLD active	t _{HLCH}		40		ns	
Clock high setup time before HOLD active	t _{CHHL}	_	60	—	ns	
Clock high setup time before HOLD not	t _{сннн}		60		ns	
active						
Output disable time	t _{SHQZ}	t _{DIS}	_	100	ns	2
Clock low to output valid	t _{CLQV}	t _V	_	70	ns	
Output hold time	t _{CLQX}	t _{HO}	0	—	ns	
Output rise time	t _{QLQH}	t _{RO}		50	ns	2
Output fall time	t _{QHQL}	t _{FO}	_	50	ns	2
HOLD high to output low-Z	t _{HHQX}	t _{LZ}		50	ns	2
HOLD low to output high-Z	t _{HLQZ}	t _{HZ}	_	100	ns	2
Write time	t _W	t _{WC}	_	5	ms	

Notes: 1. $t_{CH} + t_{CL} \ge 1/f_C$

2. Not 100% tested.



R1EX25002Axx00I/R1EX25004Axx00I

Parameter	Symbol	Alt	Min	Max	Unit	Notes
Clock frequency	f _C	f _{SCK}	_	3	MHz	
S active setup time	t _{SLCH}	t _{CSS1}	100	_	ns	
S not active setup time	t _{shCh}	t _{CSS2}	100	_	ns	
S deselect time	t _{SHSL}	t _{cs}	150		ns	
S active hold time	t _{CHSH}	t _{CSH}	100		ns	
S not active hold time	t _{CHSL}	_	100	—	ns	
Clock high time	t _{CH}	t _{CLH}	150	_	ns	1
Clock low time	t _{CL}	t _{CLL}	150	_	ns	1
Clock rise time	t _{CLCH}	t _{RC}	—	1	μs	2
Clock fall time	t _{CHCL}	t _{FC}	—	1	μs	2
Data in setup time	t _{DVCH}	t _{DSU}	30	—	ns	
Data in hold time	t _{CHDX}	t _{DH}	50	—	ns	
Clock low hold time after HOLD not active	t _{HHCH}	_	140	—	ns	
Clock low hold time after HOLD active	t _{HLCH}	_	90	—	ns	
Clock high setup time before HOLD active	t _{CHHL}		120		ns	
Clock high setup time before HOLD not active	t _{CHHH}		120	—	ns	
Output disable time	t _{SHQZ}	t _{DIS}	_	200	ns	2
Clock low to output valid	t _{CLQV}	t _V		120	ns	
Output hold time	t _{CLQX}	t _{HO}	0	_	ns	
Output rise time	t _{QLQH}	t _{RO}	_	100	ns	2
Output fall time	t _{QHQL}	t _{FO}	_	100	ns	2
HOLD high to output low-Z	t _{HHQX}	t _{LZ}	_	100	ns	2
HOLD low to output high-Z	t _{HLQZ}	t _{HZ}	—	100	ns	2
Write time	t _{vv}	t _{WC}	_	5	ms	

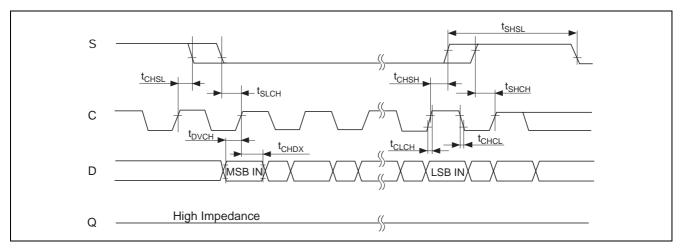
Notes: 1. $t_{CH} + t_{CL} \ge 1/f_C$

2. Not 100% tested.

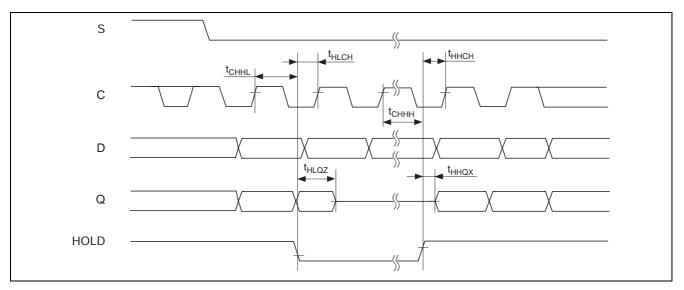


Timing Waveforms

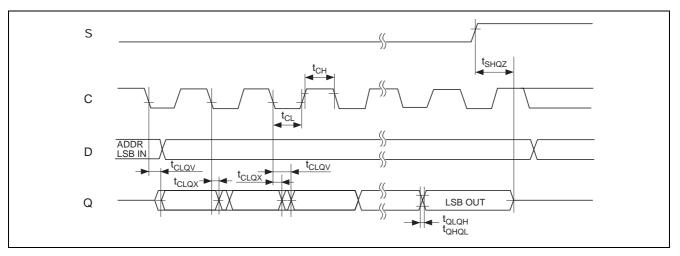
Serial Input Timing



Hold Timing



Output Timing





Pin Function

Serial data output (Q)

This output signal is used to transfer data serially out of the device. Data is shifted out on the falling edge of serial clock (C).

Serial data input (D)

This input signal is used to transfer data serially into the device. It receives instructions, addresses, and the data to be written. Values are latched on the rising edge of serial clock (C).

Serial clock (C)

This input signal provides the timing of the serial interface. Instructions, addresses, or data present at serial data input (D) are latched on the rising edge of serial clock (C). Data on serial data output (Q) changes after the falling edge of serial clock (C).

Chip select (S)

When this input signal is high, the device is deselected and serial data output (Q) is at high impedance. Unless an internal write cycle is in progress, the device will be in the standby mode. Driving chip select (S) low enables the device, placing it in the active power mode. After power-up, a falling edge on chip select (S) is required prior to the start of any instruction.

Hold (HOLD)

The hold (HOLD) signal is used to pause any serial communications with the device without deselecting the device. During the hold condition, the serial data output (Q) is high impedance, and serial data input (D) and serial clock (C) are don't care. To start the hold condition, the device must be selected, with chip select (S) driven low.

Write protect (W)

This input signal is used to protect the memory against write instructions. When write protect (W) is held low, write instructions (WRSR, WRITE) are ignored. No action on this signal can interrupt a write cycle that has already started.

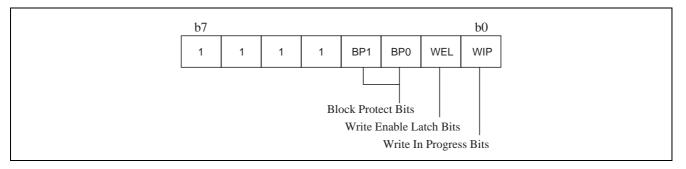


Functional Description

Status Register

The following figure shows the Status Register Format. The Status Register contains a number of status and control bits that can be read or set (as appropriate) by specific instructions.

Status Register Format



WIP bit: The Write In Progress (WIP) bit indicates whether the memory is busy with a Write or Write Status Register cycle.

WEL bit: The Write Enable Latch (WEL) bit indicates the status of the internal Write Enable Latch.

BP1, BP0 bits: The Block Protect (BP1, BP0) bits are non-volatile. They define the size of the area to be protected against Write instructions.

Instructions

Each instruction starts with a single-byte code, as summarized in the following table . If an invalid instruction is sent (one not contained in the following table), the device automatically deselects itself.

Instruction Set

Instruction	Description	Instruction Format
WREN	Write Enable	0000 ×110
WRDI	Write Disable	0000 ×100
RDSR	Read Status Register	0000 ×101
WRSR	Write Status Register	0000 ×001
READ	Read from Memory Array	0000 A011
WRITE	Write to Memory Array	0000 A010

Notes: 1. " \times " is Don't care.

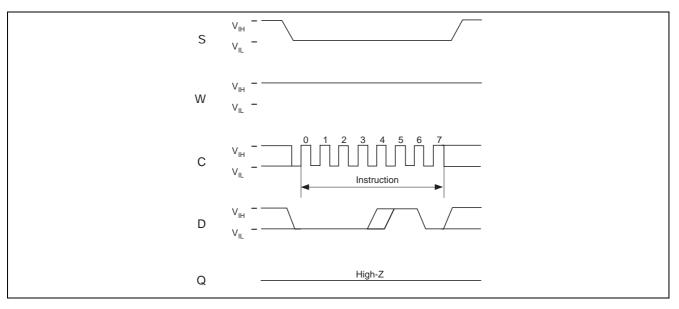
2. "A" is A_8 address on the R1EX25004A, and Don't care on the R1EX25002A.



Write Enable (WREN):

The Write Enable Latch (WEL) bit must be set prior to each WRITE and WRSR instruction. The only way to do this is to send a Write Enable instruction to the device. As shown in the following figure, to send this instruction to the device, chip select (S) is driven low, and the bits of the instruction byte are shifted in, on serial data input (D). The device then enters a wait state. It waits for the device to be deselected, by chip select (S) being driven high.

Write Enable (WREN) Sequence





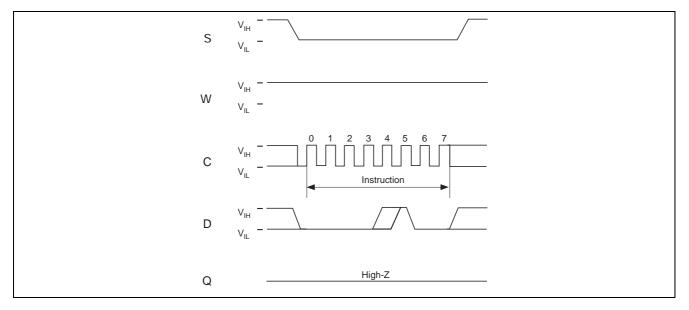
Write Disable (WRDI):

One way of resetting the Write Enable Latch (WEL) bit is to send a Write Disable instruction to the device. As shown in the following figure, to send this instruction to the device, chip select (S) is driven low, and the bits of the instruction byte are shifted in, on serial data input (D).

The device then enters a wait state. It waits for the device to be deselected, by chip select (S) being driven high. The Write Enable Latch (WEL) bit, in fact, becomes reset by any of the following events:

- Power-up
- WRDI instruction execution
- WRSR instruction completion
- WRITE instruction completion
- WRITE protect (W) is driven low

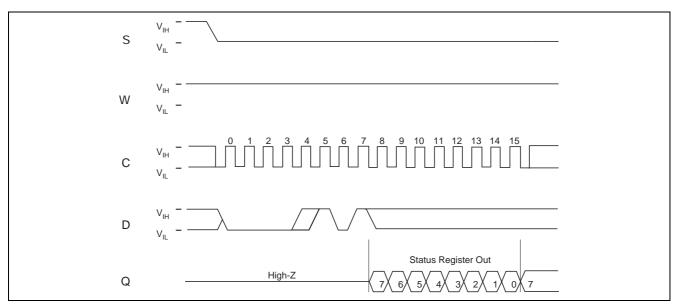
Write Disable (WRDI) Sequence





Read Status Register (RDSR):

The Read Status Register (RDSR) instruction allows the Status Register to be read. The Status Register may be read at any time, even while a Write or Write Status Register cycle is in progress. When one of these cycles is in progress, it is recommended to check the Write In Progress (WIP) bit before sending a new instruction to the device. It is also possible to read the Status Register continuously, as shown in the following figure.



Read Status Register (RDSR) Sequence

The status and control bits of the Status Register are as follows:

WIP bit: The Write In Progress (WIP) bit indicates whether the memory is busy with a Write or Write Status Register cycle. When set to 1, such a cycle is in progress. When reset to 0, no such cycles are in progress.

WEL bit: The Write Enable Latch (WEL) bit indicates the status of the internal Write Enable Latch. When set to 1, the internal Write Enable Latch is set. When set to 0, the internal Write Enable Latch is reset and no Write or Write Status Register instructions are accepted.

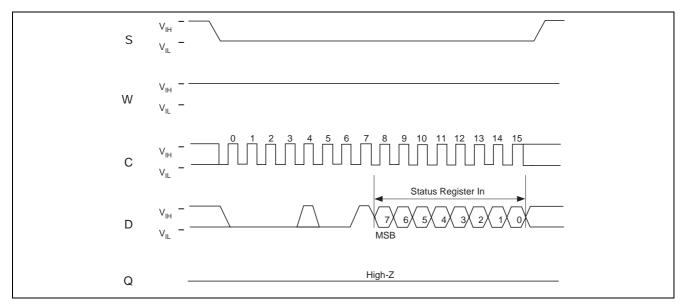
BP1, BP0 bits: The Block Protect (BP1, BP0) bits are non-volatile. They define the size of the area to be software protected against Write instructions. These bits are written with the Write Status Register (WRSR) instruction. When one or both of the Block Protect (BP1, BP0) bits are set to 1, the relevant memory area (as defined in the Status Register Format table) becomes protected against Write (WRITE) instructions. The Block Protect (BP1, BP0) bits can be written provided that the Hardware Protected mode has not been set.



Write Status Register (WRSR):

The Write Status Register (WRSR) instruction allows new values to be written to the Status Register. Before it can be accepted, a Write Enable (WREN) instruction must previously have been executed. After the Write Enable (WREN) instruction has been decoded and executed, the device sets the Write Enable Latch(WEL). The instruction sequence is shown in the following figure. The Write Status Register (WRSR) instruction has no effect on b6, b5, b4, b1 and b0 of the Status Register. b6, b5 and b4 are always read as 0. Chip select (S) must be driven high after the rising edge of serial clock (C) that latches in the eighth bit of the data byte, and before the next rising edge of serial clock (C). Otherwise, the Write Status Register (WRSR) instruction is not executed. As soon as chip select (S) is driven high, the self-timed Write Status Register may still be read to check the value of the Write In Progress (WIP) bit. The Write In Progress (WIP) bit is 1 during the self-timed Write Status Register cycle, and is 0 when it is completed. When the cycle is completed, Write Enable Latch(WEL) is reset. The Write Status Register (WRSR) instruction allows the user to change the values of the Block Protect (BP1, BP0) bits, to define the size of the area that is to be treated as read-only, as defined in the Status Register Format table.

The contents of Block Protect (BP1, BP0) bits are frozen at their current values just before the start of the execution of the Write Status Register (WRSR) instruction. The new, updated values take effect at the moment of completion of the execution of Write Status Register (WRSR) instruction.



Write Status Register (WRSR) Sequence



Read from Memory Array (READ):

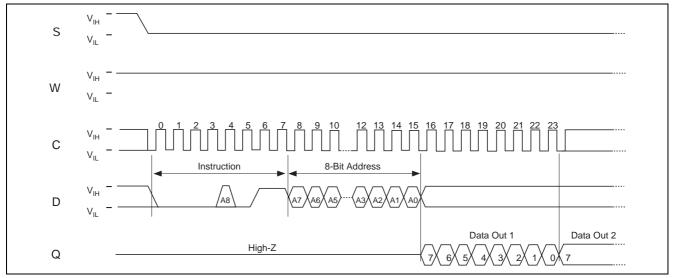
As shown in the following figure, to send this instruction to the device, chip select (S) is first driven low. The bits of the instruction byte and the address bytes are then shifted in, on serial data input (D). The addresses are loaded into an internal address register, and the byte of data at that address is shifted out, on serial data output (Q). The most significant address (A8) should be sent as fifth bit in the instruction byte.

If chip select (S) continues to be driven low, the internal address register is automatically incremented, and the byte of data at the new address is shifted out.

When the highest address is reached, the address counter rolls over to zero, allowing the Read cycle to be continued indefinitely. The whole memory can, therefore, be read with a single READ instruction.

The Read cycle is terminated by driving chip select (S) high. The rising edge of the chip select (S) signal can occur at any time during the cycle. The addressed first byte can be any byte within any page. The instruction is not accepted, and is not executed, if a Write cycle is currently in progress.

Read from Memory Array (READ) Sequence



Note: 1. Depending on the memory size, as shown in the following table, the most significant address bits are don't care.

Address Range Bits

Device	R1EX25004A	R1EX25002A
Address bits	A8 to A0	A7 to A0

Note: 1. A8 is don't care on the R1EX25002A.



Write to Memory Array (WRITE):

As shown in the following figure, to send this instruction to the device, chip select (S) is first driven low. The bits of the instruction byte, address byte, and at least one data byte are then shifted in, on serial data input (D).

The instruction is terminated by driving chip select (S) high at a byte boundary of the input data. In the case of the following figure, this occurs after the eighth bit of the data byte has been latched in, indicating that the instruction is being used to write a single byte. The self-timed Write cycle starts, and continues for a period t_{WC} (as specified in AC Characteristics). At the end of the cycle, the Write In Progress (WIP) bit is reset to 0.

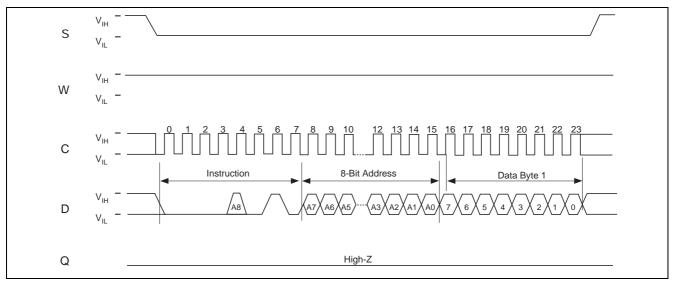
If, though, chip select (S) continues to be driven low, as shown in the following figure, the next byte of the input data is shifted in, so that more than a single byte, starting from the given address towards the end of the same page, can be written in a single internal Write cycle.

Each time a new data byte is shifted in, the least significant bits of the internal address counter are incremented. If the number of data bytes sent to the device exceeds the page boundary, the internal address counter rolls over to the beginning of the page, and the previous data there are overwritten with the incoming data. (The page size of these device is 32 bytes).

The instruction is not accepted, and is not executed, under the following conditions:

- If the Write Enable Latch (WEL) bit has not been set to 1 (by executing a Write Enable instruction just before)
- If a Write cycle is already in progress
- If the addressed page is in the region protected by the Block Protect (BP1 and BP0) bits.
- If Write Protect (W) is low

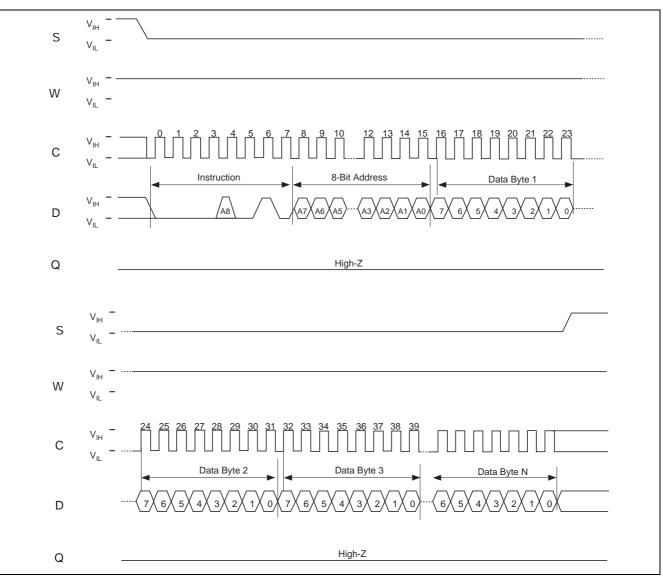
Byte Write (WRITE) Sequence (1 Byte)



Note: 1. Depending on the memory size, as shown in Address Range Bits table, the most significant address bit is don't care.



Byte Write (WRITE) Sequence (Page)



Note: 1. Depending on the memory size, as shown in Address Range Bits table, the most significant address bit is don't care.



Data Protect

The Block Protect bits (BP1, BP0) define the area of memory that is protected against the execution of write cycle, as summarized in the following table.

When Write Protect (W) is driven low, write to memory array (WRITE) and write status register (WRSR) are disabled, and WEL bit is reset.

Write Protected Block Size

Status re	egister bits		Array addres	ses protected
BP1	BP0	Protected blocks	R1EX25004A	R1EX25002A
0	0	None	None	None
0	1	Upper quarter	180h – 1FFh	C0h – FFh
1	0	Upper half	100h – 1FFh	80h – FFh
1	1	Whole memory	000h – 1FFh	00h – FFh

Hold Condition

The hold (HOLD) signal is used to pause any serial communications with the device without resetting the clocking sequence.

During the hold condition, the serial data output (Q) is high impedance, and serial data input (D) and serial clock (C) are don't care.

To enter the hold condition, the device must be selected, with chip select (S) low.

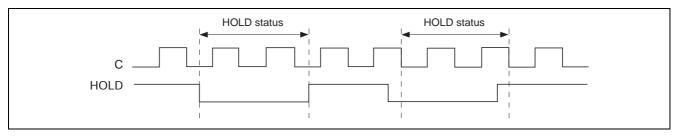
Normally, the device is kept selected, for the whole duration of the hold condition. Deselecting the device while it is in the hold condition, has the effect of resetting the state of the device, and this mechanism can be used if it is required to reset any processes that had been in progress.

The hold condition starts when the hold (HOLD) signal is driven low at the same time as serial clock (C) already being low (as shown in the following figure).

The hold condition ends when the hold (HOLD) signal is driven high at the same time as serial clock (C) already being low.

The following figure also shows what happens if the rising and falling edges are not timed to coincide with serial clock (C) being low.

Hold Condition Activation





Notes

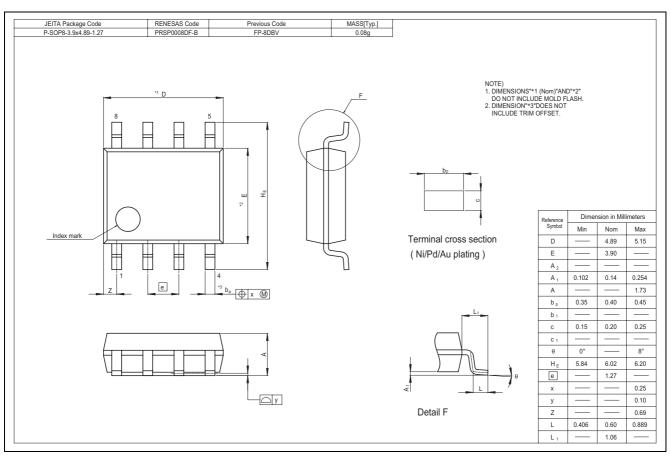
Data Protection at V_{cc} On/Off

When V_{CC} is turned on or off, noise on S inputs generated by external circuits (CPU, etc) may act as a trigger and turn the EEPROM to unintentional program mode. To prevent this unintentional programming, this EEPROM have a power on reset function. Be careful of the notices described below in order for the power on reset function to operate correctly.

- S should be fixed to V_{CC} during V_{CC} on/off. Low to high or high to low transition during V_{CC} on/off may cause the trigger for the unintentional programming.
- \bullet V_{CC} should be turned on/off after the EEPROM is placed in a standby state.
- V_{CC} should be turned on from the ground level (V_{SS}) in order for the EEPROM not to enter the unintentional programming mode.
- V_{CC} turn on speed should be slower than 10 μ s/V.
- When WRSR or WRITE instruction is executed before V_{CC} turns off, V_{CC} should be turned off after waiting write cycle time (t_W).



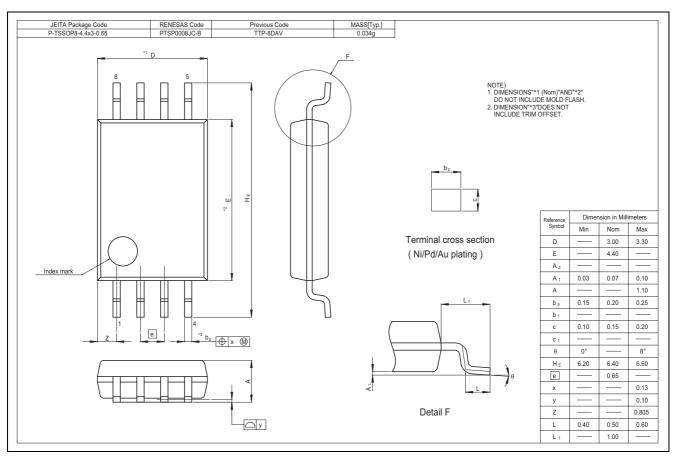
Package Dimensions



R1EX25002ASA00I/R1EX25004ASA00I (PRSP0008DF-B / Previous Code: FP-8DBV)









Rev.	Date	Contents of Modification	
		Page	Description
0.01	Feb.21, 2008		Initial issue
0.02	Jan.09, 2009	P1	Features
			Endurance cycles change 10 ⁶ cycles to 1,000k cycles @25°C.
			Data retentions years change 10 years to 100 years @25°C.
		P3	Capacitance new is described.
			Memory cell characteristics new is described.
		P4	DC characteristics
			Output voltage V_{OH1} , V_{OH2} test conditions change I_{oL} to $I_{oH.}$
		P5/P6	AC characteristics
			Erase/Write endurance is deleted.
			Notes1. change Not 100% tested.
			Notes3 deleted.

RenesasTechnology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Benesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
 Pines
 This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warranties or representations with respect to the accuracy or completeness of the information in this document.
 But not infinited in product data. diagrams, charts, programs, algorithms, and application scule as the development of wappons of mass and regulations.
 Autor of the purpose of any other military use. When exporting the products or the technology described herein, you should follow the applicable export control laws and regulations, and proceedures required by such laws and regulations.
 All information included in this document, such as product data, diagrams, charts, programs, algorithms, and application scule as the development of wappons of mass destruction or for the purpose of any other military use. When exporting the products or the technology described herein, you should follow the applicable export control laws and regulations, and proceedures required by such laws and regulations.
 Renesas has used reasonable care in compiling the information in this document, but Renesas assumes no liability whattosever for any damages incurred as a fast used reasonable care in compiling the information in this document, but Renesas assumes no liability whattosever for any damages incurred as a disclosed by Renesas states and splications, and process as and splication state and splication state and splication and applications and regulations.
 Renesas hall was the site of the data disclosed through explication in the data this document.
 When using or otherwise regulation the information in this document. Dut Renesas assumes no liability whattosever for any damages incurred as a disclosed by Renesas as stule or mato the data disclosed through Renes



RENESAS SALES OFFICES

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

http://www.renesas.com